



# BC856BMB

60 V, 100 mA PNP general-purpose transistor

19 August 2015

Product data sheet

## 1. General description

PNP general-purpose transistor in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: BC846BMB.

## 2. Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

## 3. Applications

- General-purpose switching and amplification
- Mobile applications

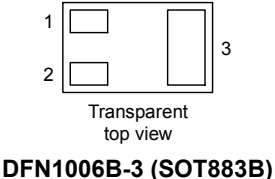
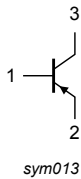
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-60	V
$I_C$	collector current		-	-	-100	mA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}$ ; $I_C = -2\text{ mA}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	220	-	475	

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	E	emitter		
3	C	collector		



## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC856BMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BC856BMB	0101 1010

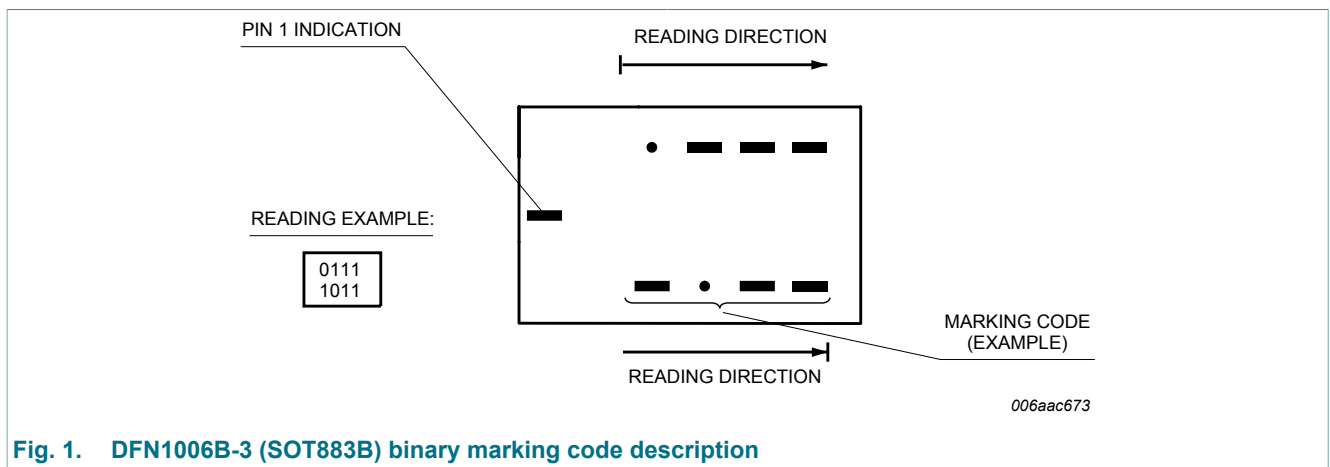


Fig. 1. DFN1006B-3 (SOT883B) binary marking code description

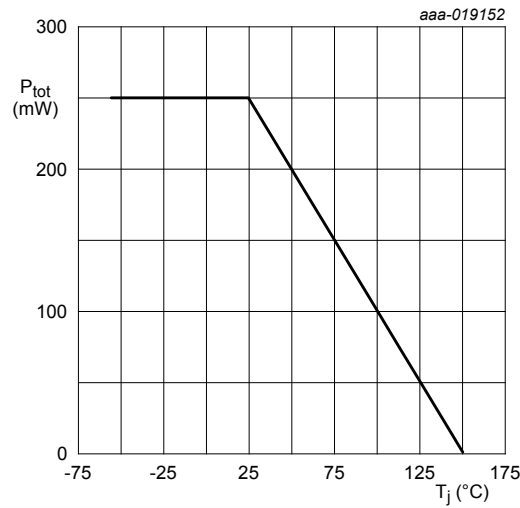
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-80	V
$V_{CEO}$	collector-emitter voltage	open base		-	-60	V
$V_{EBO}$	emitter-base voltage	open collector		-	-6	V
$I_C$	collector current			-	-100	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms		-	-200	mA
$I_{BM}$	peak base current			-	-200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	250	mW
$T_j$	junction temperature			-	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

**Fig. 2. Power derating curve DFN1006B-3 (SOT883B)**

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

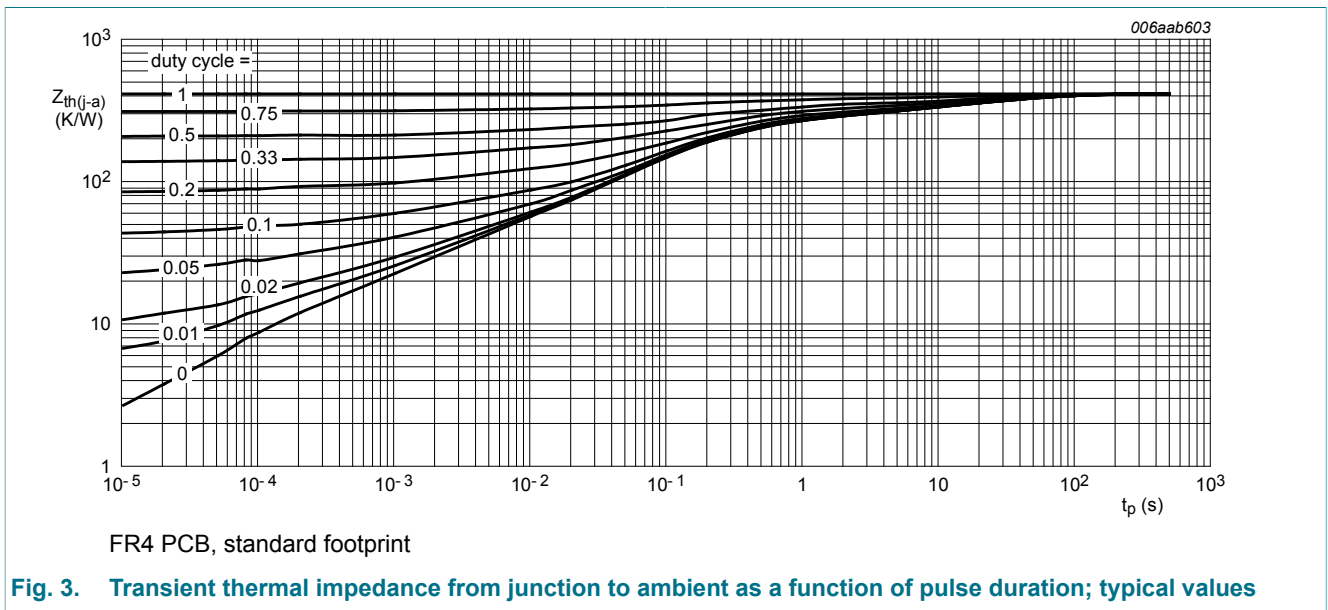
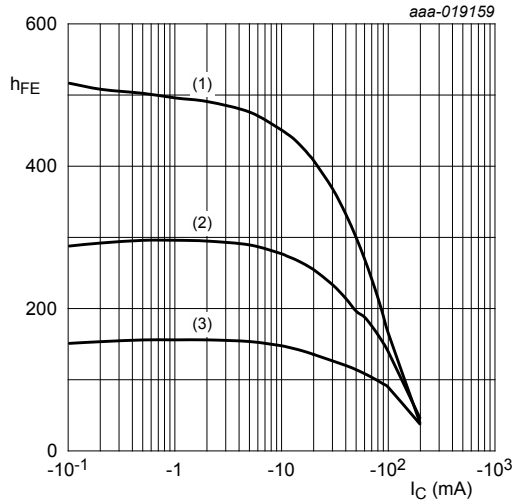


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

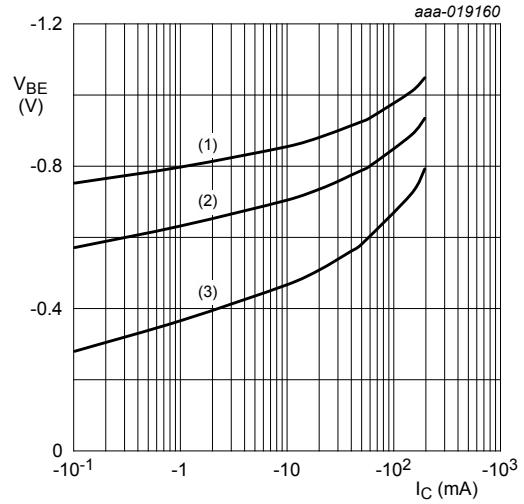
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-15	nA
		V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C	220	-	475	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA; T <sub>amb</sub> = 25 °C	-	-	-200	mV
		I <sub>C</sub> = -100 mA; I <sub>B</sub> = -5 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-400	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA; T <sub>amb</sub> = 25 °C	-	-700	-	mV
		I <sub>C</sub> = -100 mA; I <sub>B</sub> = -5 mA; T <sub>amb</sub> = 25 °C	-	-850	-	mV
V <sub>BE</sub>	base-emitter voltage	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C	-600	-	-750	mV
		V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C	-	-	-820	mV
C <sub>C</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	2.5	pF
C <sub>E</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	4.5	-	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	-	-	MHz
NF	noise figure	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -200 μA; R <sub>S</sub> = 2 kΩ; f = 1 kHz; B = 200 Hz; T <sub>amb</sub> = 25 °C	-	-	10	dB



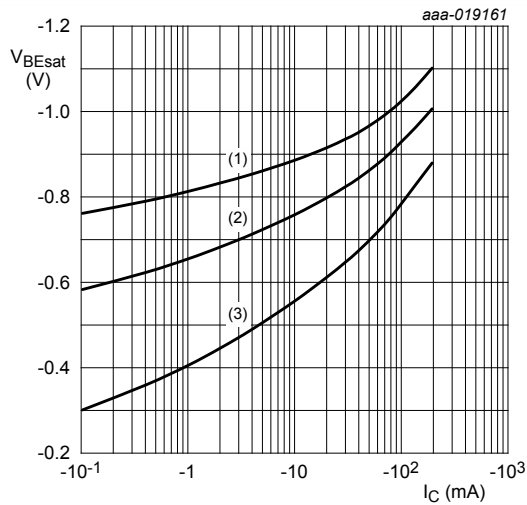
$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = 150^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = -55^\circ\text{C}$

**Fig. 4. DC current gain as a function of collector current; typical values**



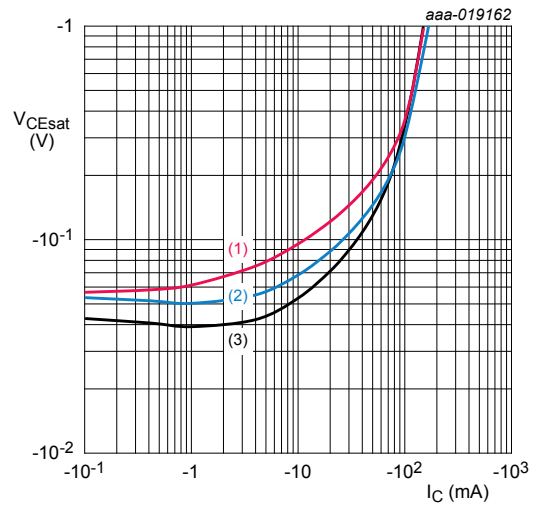
$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = -55^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = 150^\circ\text{C}$

**Fig. 5. Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = -55^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = 150^\circ\text{C}$

**Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 150^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = -55^\circ\text{C}$

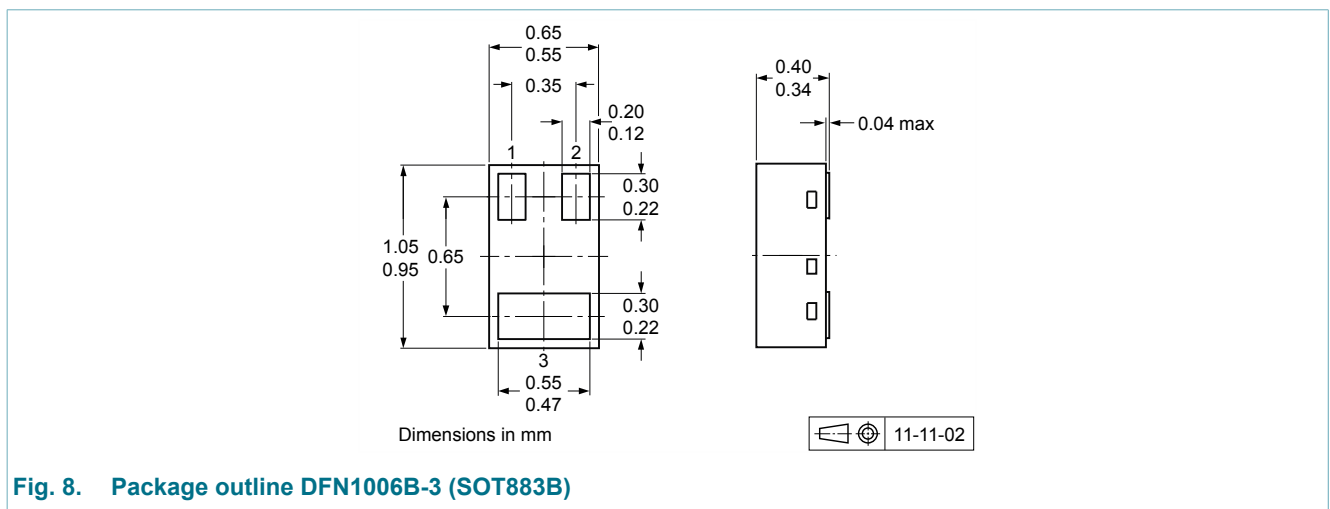
**Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values**

## 11. Test information

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



### 13. Soldering

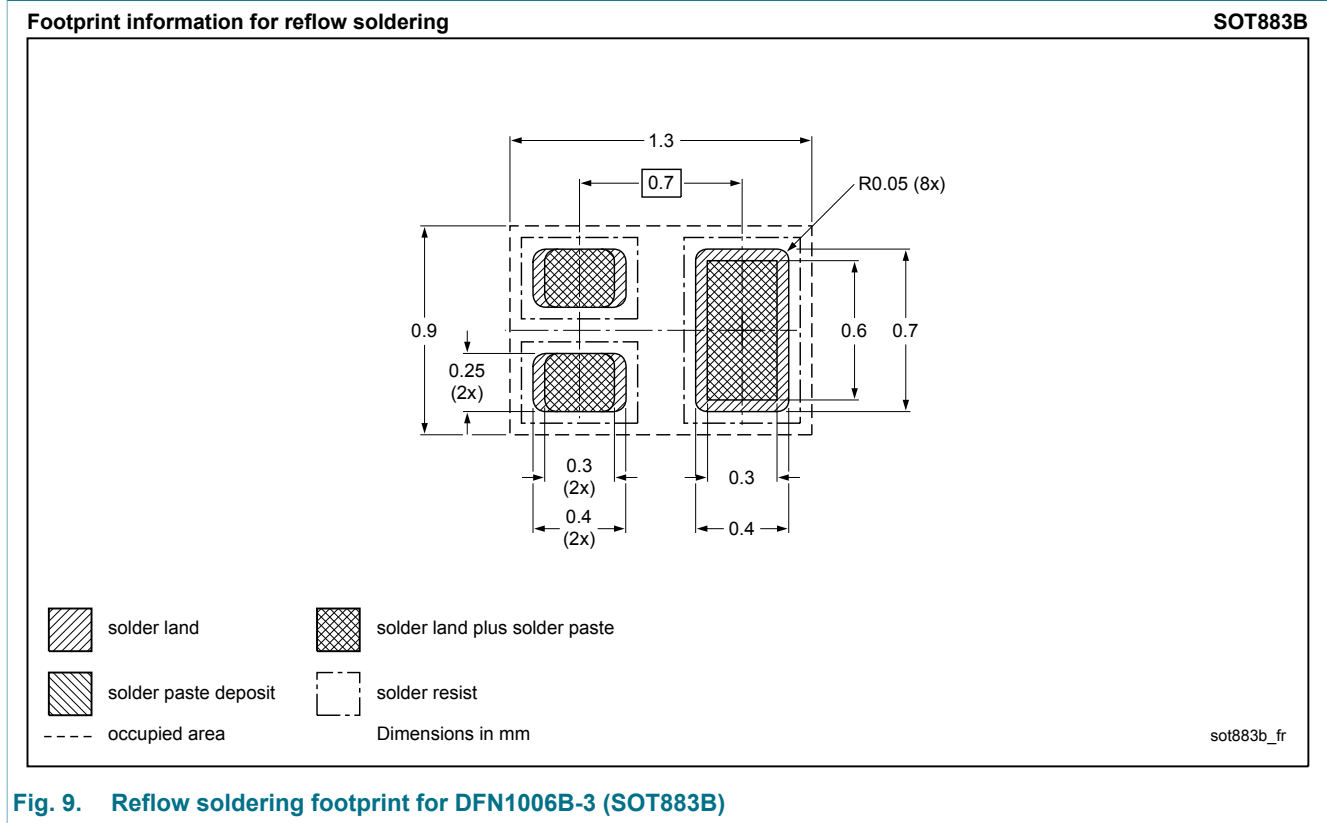


Fig. 9. Reflow soldering footprint for DFN1006B-3 (SOT883B)



## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC856BMB v.1	20150819	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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